

## IN THE CLAIMS

The following listing of claims replaces all prior listings:

1. (currently amended) A method for manufacturing a micromachine ~~including an oscillator, comprising the steps of:~~
  - forming a lower wire;
  - forming a first sacrifice layer comprising silicon dioxide and covering a top surface of the lower wire;
  - forming an oscillator on a portion of the first sacrifice layer;
  - ~~a step of forming a second sacrifice layer around a movable portion of the on the top and side surfaces of the oscillator, the second sacrificial layer comprising silicon dioxide;~~
  - ~~a step of covering the exposed portions of the first and second sacrifice layer layers with an overcoat film, followed by the formation of a penetrating hole extending through the overcoat film to reach reaching the first sacrifice layer in the overcoat layer;~~
  - ~~a step of performing sacrifice-layer etching which removes the sacrifice layer using the penetrating hole in order to form a space around the movable portion; and~~
  - ~~a step of performing a film-formation treatment by sputtering at a reduced pressure following the sacrifice-layer etching so as to form a sputtering layer that seals the penetrating hole and which is formed into at least one upper wire over the overcoat film,~~

wherein,

the sputtering layer is composed of one selected from the group consisting of an aluminum copper film and an aluminum silicon film.
2. (original) The method for manufacturing a micromachine, according to claim 1, wherein the method is applied to a micromachine having means for driving oscillation in the oscillator.
3. (original) The method for manufacturing a micromachine, according to claim 2, wherein static electricity is used as the means for driving oscillation.

4. (original) The method for manufacturing a micromachine, according to claim 2, wherein piezoelectricity is used as the means for driving oscillation.

5. (cancelled)